

Silicon N-Channel MOSFET Triode

- For high-frequency stages up to 300 MHz preferably in FM applications
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BF999	LBs	1=G	2=D	3=S	-	-	-	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	20	V
Continuous drain current	I_D	30	mA
Gate-source peak current	$\pm I_{GSM}$	10	mA
Total power dissipation $T_S \leq 76 \text{ }^\circ\text{C}$	P_{tot}	200	mW
Storage temperature	T_{stg}	-55 ... 150	°C
Channel temperature	T_{ch}	150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Channel - soldering point ²⁾	R_{thchs}	≤ 370	K/W

¹Pb-containing package may be available upon special request

²For calculation of R_{thJA} please refer to Application Note Thermal Resistance

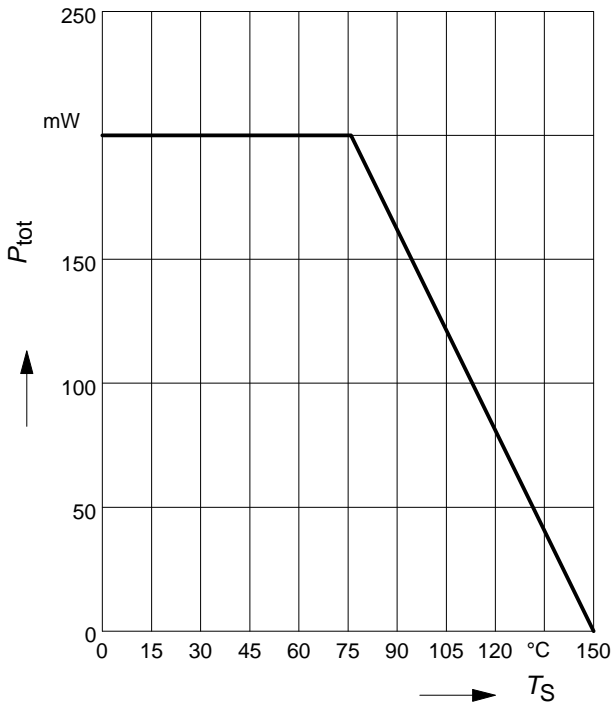
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Drain-source breakdown voltage $I_D = 10 \mu\text{A}, -V_{GS} = 4 \text{ V}$	$V_{(BR)DS}$	20	-	-	V
Gate-source breakdown voltage $\pm I_{GS} = 10 \text{ mA}, V_{DS} = 0$	$\pm V_{(BR)GSS}$	6.5	-	12	
Gate-source leakage current $\pm V_{GS} = 5 \text{ V}, V_{DS} = 0$	$\pm I_{GSS}$	-	-	50	nA
Drain current $V_{DS} = 10 \text{ V}, V_{GS} = 0$	I_{DSS}	5	10	16	mA
Gate-source pinch-off voltage $V_{DS} = 10 \text{ V}, I_D = 20 \mu\text{A}$	$-V_{GS(p)}$	-	0.8	1.5	V

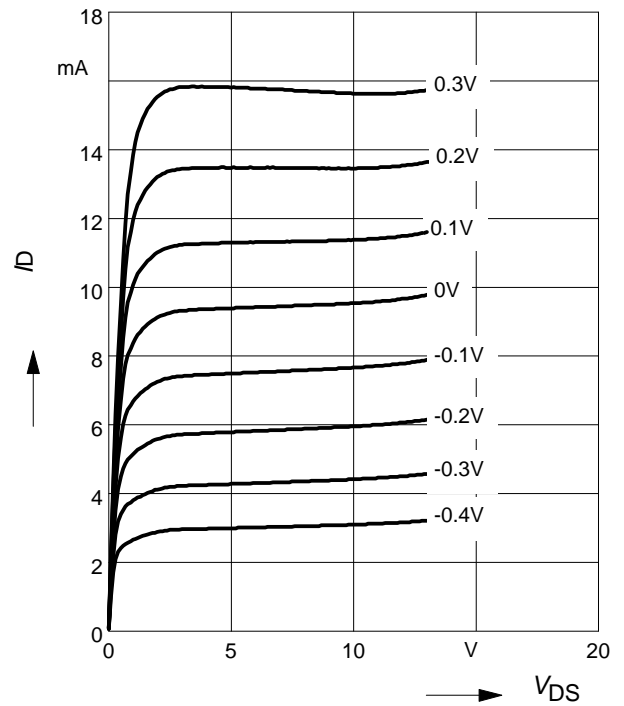
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Forward transconductance $V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}$	g_{fs}	14	20	-	mS
Gate input capacitance $V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}, f = 10 \text{ MHz}$	C_{gss}	-	2.5	-	pF
Output capacitance $V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}, f = 10 \text{ MHz}$	C_{dss}	-	0.9	-	pF
Power gain $V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}, f = 45 \text{ MHz}$	G_p	-	27	-	dB
Noise figure $V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}, f = 45 \text{ MHz}$	F	-	2.1	-	dB

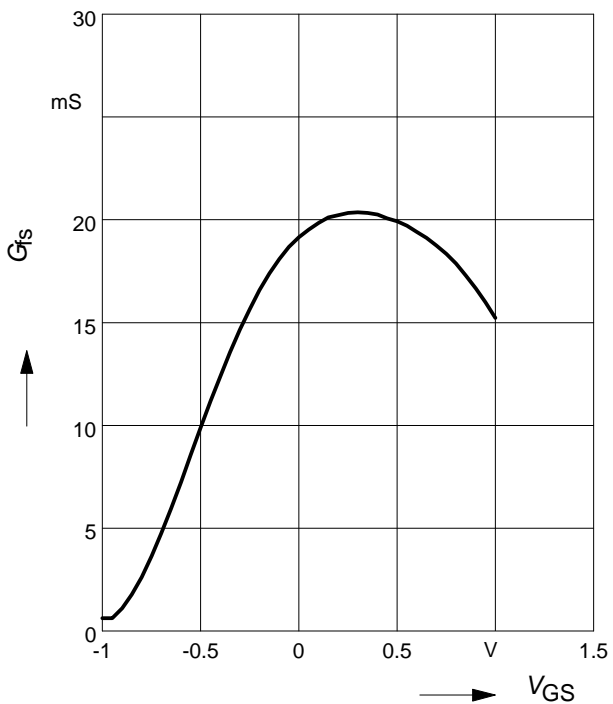
Total power dissipation $P_{tot} = f(T_S)$



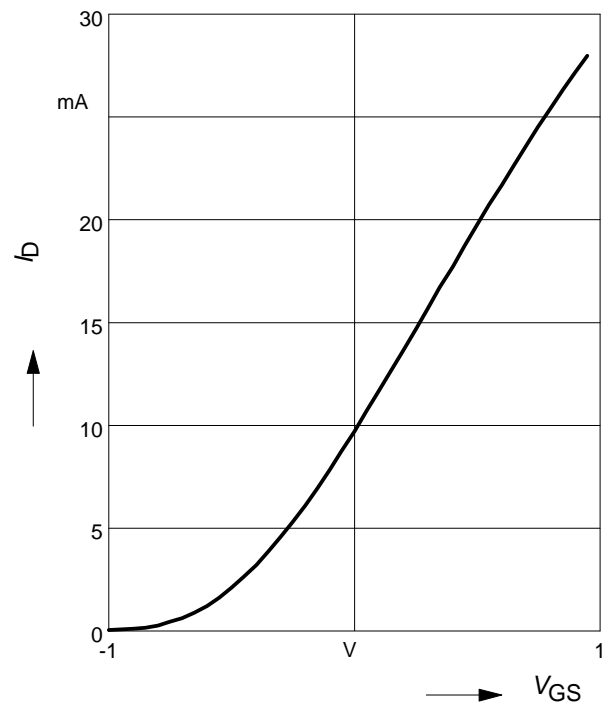
Output characteristics $I_D = f(V_{DS})$



Gate transconductance $g_{fs} = f(V_{GS})$

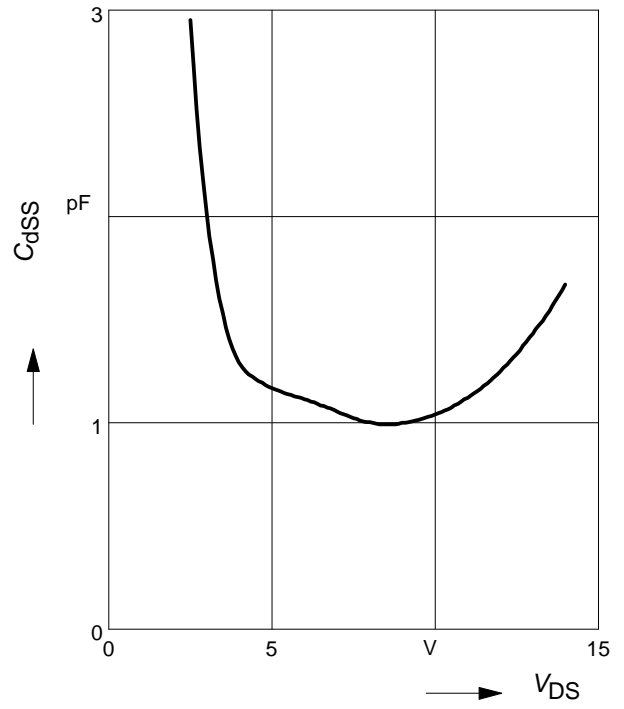
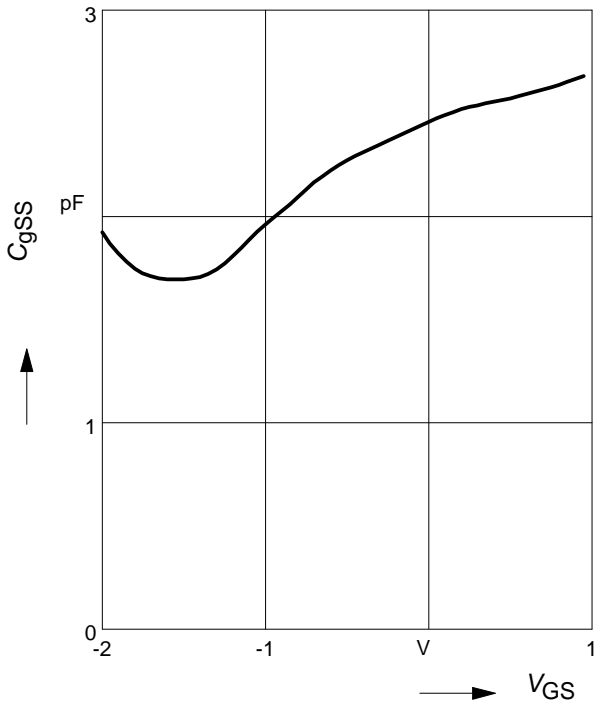


Drain current $I_D = f(V_{GS})$



Gate input capacitance $C_{gss} = f(V_{GS})$

Output capacitance $C_{dss} = f(V_{DS})$

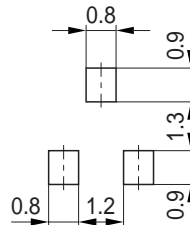


Package Outline



1) Lead width can be 0.6 max. in dambar area

Foot Print



Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



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